

RoHS Compliant Product

Description

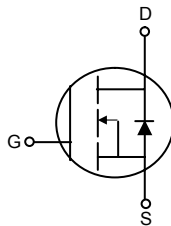
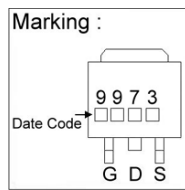
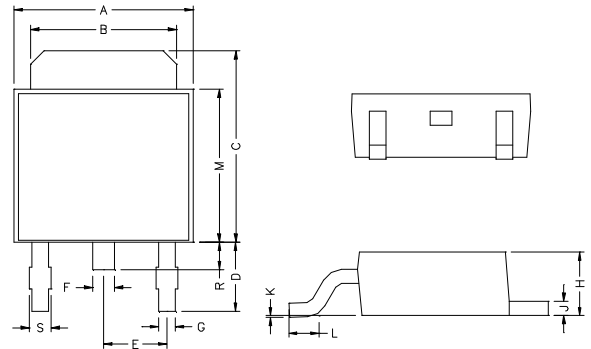
The SSD9973 provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness.

The TO-252 is universally preferred for all commercial-industrial surface mount applications and suited for low voltage applications such as DC/DC converters.

Features

- * Low Gate Charge
- * Simple Drive Requirement

TO-252



| REF. | Millimeter | | REF. | Millimeter | |
|------|------------|------|------|------------|------|
| | Min. | Max. | | Min. | Max. |
| A | 6.40 | 6.80 | G | 0.50 | 0.70 |
| B | 5.20 | 5.50 | H | 2.20 | 2.40 |
| C | 6.80 | 7.20 | J | 0.45 | 0.55 |
| D | 2.20 | 2.80 | K | 0 | 0.15 |
| E | 2.30 REF. | | L | 0.90 | 1.50 |
| F | 0.70 | 0.90 | M | 5.40 | 5.80 |
| S | 0.60 | 0.90 | R | 0.80 | 1.20 |

Absolute Maximum Ratings

| Parameter | Symbol | Ratings | Unit |
|--|-----------------------|----------|---------------|
| Drain-Source Voltage | V_{DS} | 60 | V |
| Gate-Source Voltage | V_{GS} | ± 20 | V |
| Continuous Drain Current, $V_{GS}@10V$ | $I_D@T_C=25^\circ C$ | 14 | A |
| Continuous Drain Current, $V_{GS}@10V$ | $I_D@T_C=100^\circ C$ | 9 | A |
| Pulsed Drain Current ¹ | I_{DM} | 40 | A |
| Total Power Dissipation | $P_D@T_C=25^\circ C$ | 27 | W |
| Linear Derating Factor | | 0.22 | W/ $^\circ C$ |
| Operating Junction and Storage Temperature Range | T_j, T_{stg} | -55~+150 | $^\circ C$ |

Thermal Data

| Parameter | Symbol | Ratings | Unit |
|-------------------------------------|-------------|---------|--------------|
| Thermal Resistance Junction-case | R_{thj-c} | 4.5 | $^\circ C/W$ |
| Thermal Resistance Junction-ambient | R_{thj-a} | 110 | $^\circ C/W$ |

Electrical Characteristics(T_j=25°C Unless otherwise specified)

| Parameter | Symbol | Min. | Typ. | Max. | Unit | Test Condition |
|--|-------------------------------------|------|------|------|------|--|
| Drain-Source Breakdown Voltage | BV _{DSS} | 60 | - | - | V | V _{GS} =0V, I _D =250uA |
| Breakdown Voltage Temp. Coefficient | ΔBV _{DSS} /ΔT _j | - | 0.05 | - | V/°C | Reference to 25°C, I _D =1mA |
| Gate Threshold Voltage | V _{GS(th)} | 1.0 | - | 3.0 | V | V _{DS} =V _{GS} , I _D =250uA |
| Gate-Source Leakage Current | I _{GSS} | - | - | ±100 | nA | V _{GS} =±20V |
| Drain-Source Leakage Current (T _j =25°C) | I _{DSS} | - | - | 1 | uA | V _{DS} =60V, V _{GS} =0 |
| Drain-Source Leakage Current (T _j =150°C) | | - | - | 25 | uA | V _{DS} =48V, V _{GS} =0 |
| Static Drain-Source On-Resistance | R _{DS(ON)} | - | - | 80 | mΩ | V _{GS} =10V, I _D =9A |
| | | - | - | 100 | | V _{GS} =4.5V, I _D =6A |
| Total Gate Charge ² | Q _g | - | 8 | 13 | nC | I _D =9A V _{DS} =48V V _{GS} =4.5V |
| Gate-Source Charge | Q _{gs} | - | 3 | - | | |
| Gate-Drain ("Miller") Charge | Q _{gd} | - | 4 | - | | |
| Turn-on Delay Time ² | T _{d(ON)} | - | 7 | - | nS | V _{DD} =30V I _D =9A V _{GS} =10V R _G =3.3Ω R _D =3.3Ω |
| Rise Time | T _r | - | 15 | - | | |
| Turn-off Delay Time | T _{d(OFF)} | - | 16 | - | | |
| Fall Time | T _f | - | 3 | - | | |
| Input Capacitance | C _{iss} | - | 720 | 1150 | pF | V _{GS} =0V V _{DS} =25V f=1.0MHz |
| Output Capacitance | C _{oss} | - | 77 | - | | |
| Reverse Transfer Capacitance | C _{rss} | - | 45 | - | | |
| Forward Transconductance | G _{fs} | - | 8.6 | - | S | V _{DS} =10V, I _D =9A |

Source-Drain Diode

| Parameter | Symbol | Min. | Typ. | Max. | Unit | Test Condition |
|---------------------------------|-----------------|------|------|------|------|--|
| Forward On Voltage ² | V _{SD} | - | - | 1.2 | V | I _S =14 A, V _{GS} =0V. |
| Reverse Recovery Time | T _{rr} | - | 28 | - | nS | I _S =9 A, V _{GS} =0V. di/dt=100A/us |
| Reverse Recovery Charge | Q _{rr} | - | 27 | - | nC | |

Notes: 1.Pulse width limited by Max. junction temperature.

2.Pulse width ≤300us, dutycycle ≤2%.

Characteristics Curve

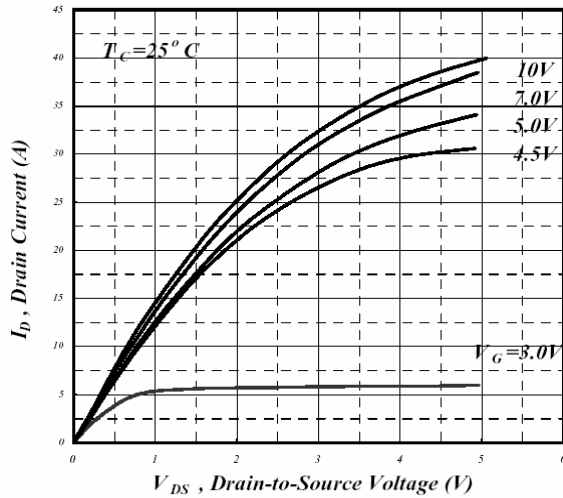


Fig 1. Typical Output Characteristics

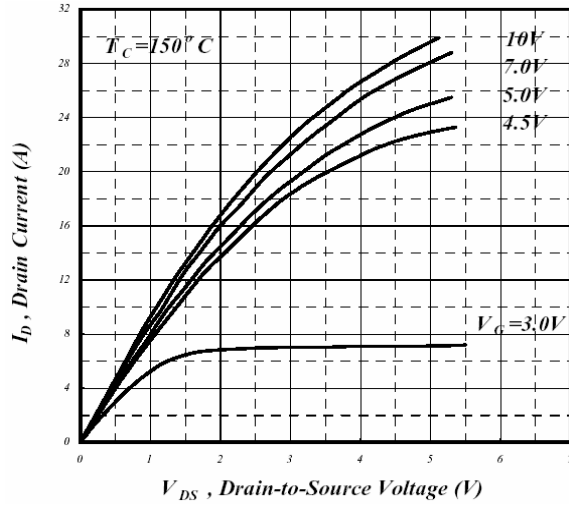


Fig 2. Typical Output Characteristics

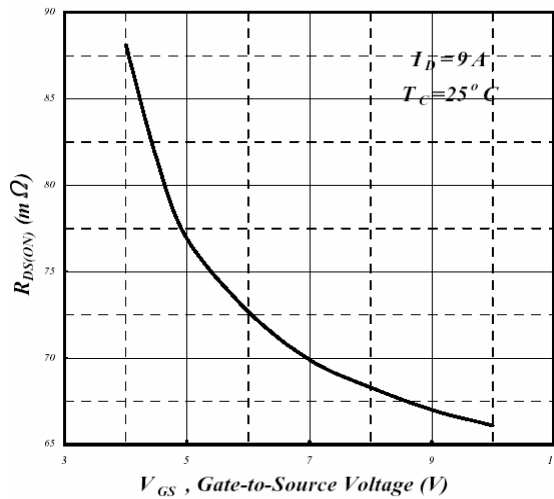


Fig 3. On-Resistance v.s. Gate Voltage

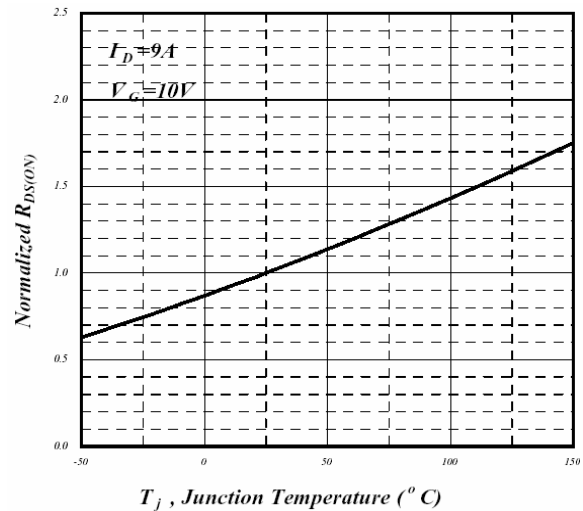


Fig 4. Normalized On-Resistance v.s. Junction Temperature

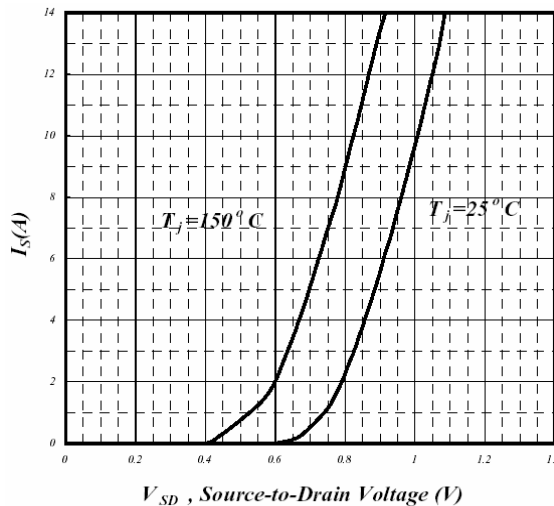


Fig 5. Forward Characteristics of Reverse Diode

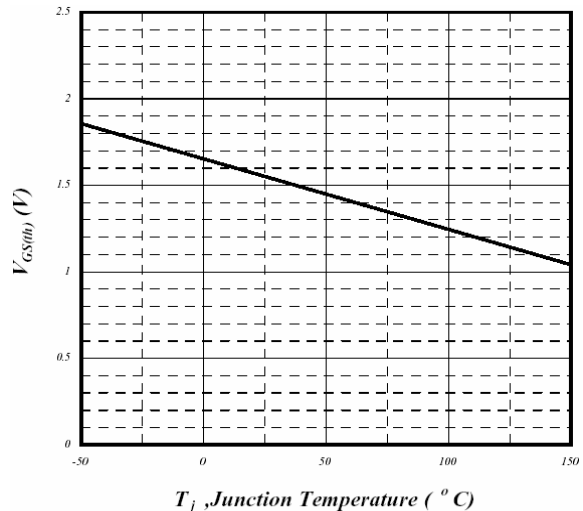


Fig 6. Gate Threshold Voltage v.s. Junction Temperature

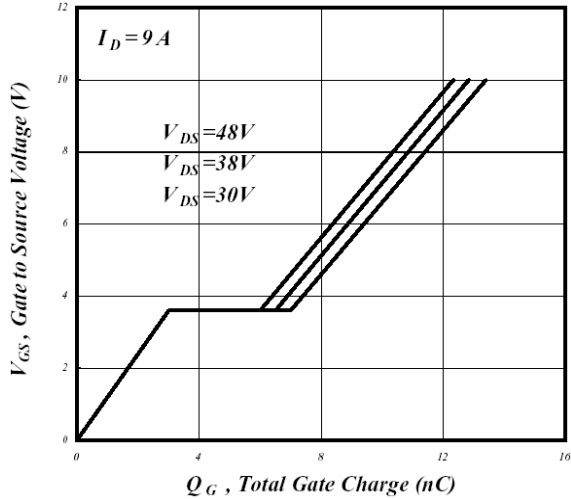


Fig 7. Gate Charge Characteristics

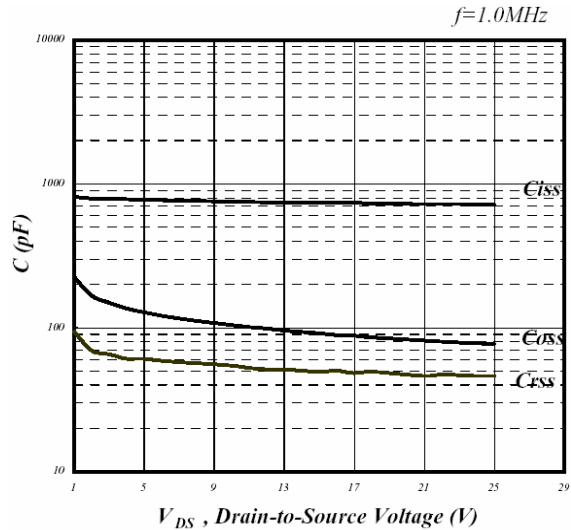


Fig 8. Typical Capacitance Characteristics

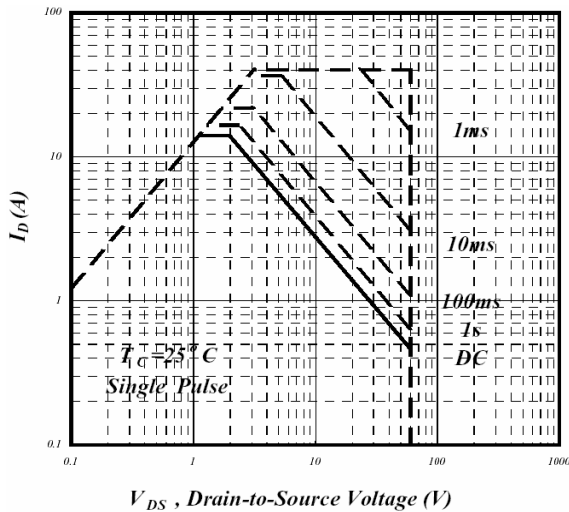


Fig 9. Maximum Safe Operating Area

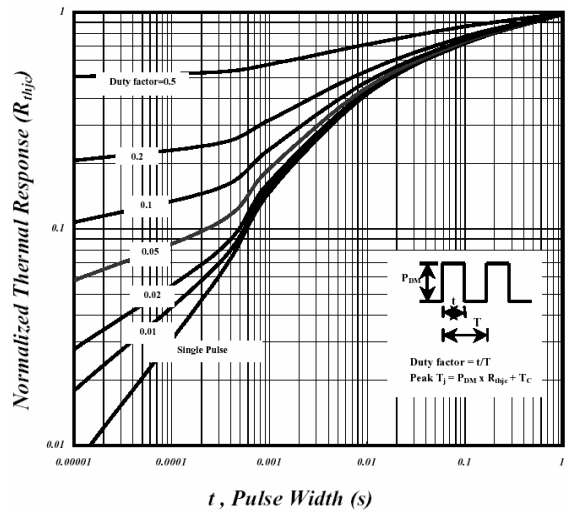


Fig 10. Effective Transient Thermal Impedance

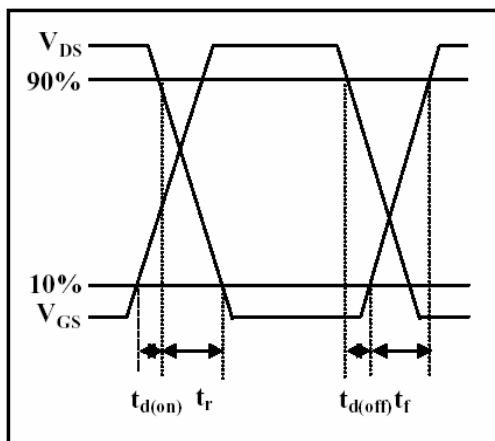


Fig 11. Switching Time Waveform

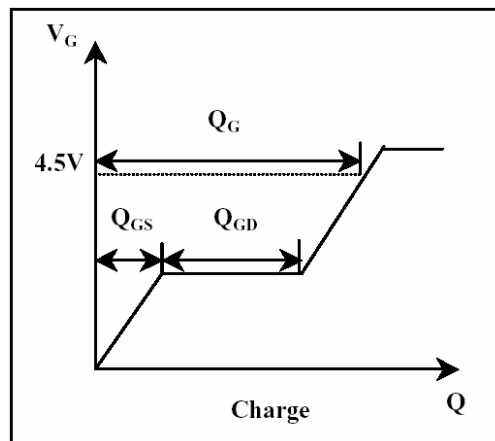


Fig 12. Gate Charge Waveform